# imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



## Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





## STTH61R04TV

## Ultrafast recovery diode

### Main product characteristics

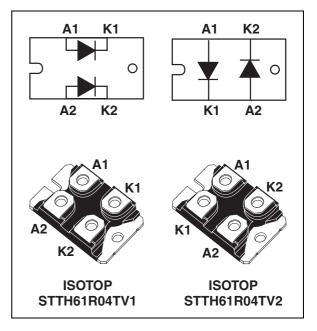
I <sub>F(AV)</sub>	2 x 30 A
V <sub>RRM</sub>	400 V
Tj	150° C
V <sub>F (typ)</sub>	0.95 V
t <sub>rr (typ)</sub>	24 ns

### Features and benefits

- Ultrafast
- Very low switching losses
- High frequency and high pulsed current operation
- Low leakage current
- Insulated package:
  - ISOTOP
     Electrical insulation = 2500 V<sub>RMS</sub>
     Capacitance = 45 pF

### Description

The STTH61R04TV series uses ST's new 400 V planar Pt doping technology. The STTH61R04 is specially suited for switching mode base drive and transistor circuits, such as welding equipment.



### **Order codes**

Part Number	Marking
STTH61R04TV1	STTH61R04TV1
STTH61R04TV2	STTH61R04TV2

## 1 Characteristics

#### Table 1. Absolute ratings (limiting values per diode at 25° C, unless otherwise specified)

Symbol	Parameter					Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage				400	V
V <sub>RSM</sub>	Non repetitive peak reverse voltage				400	V
I <sub>F(RMS)</sub>	RMS forward current			60	Α	
I <sub>F(AV)</sub>	Average forward current, $\delta = 0.5$	Per diode $T_c = 80^{\circ} C$		30	Α	
I <sub>FRM</sub>	Repetitive peak forward current	Repetitive peak forward current $t_p = 5 \ \mu s$ , F = 1 kHz square			900	А
I <sub>FSM</sub>	Surge non repetitive forward current t <sub>p</sub> = 10 ms Sinusoidal			350	Α	
T <sub>stg</sub>	Storage temperature range			-65 to + 150	°C	
Т <sub>ј</sub>	Maximum operating junction temperature			150	°C	

#### Table 2.Thermal parameters

Symbol	Parameter		Value	Unit
P	Junction to case	Per diode	1.5	
R <sub>th(j-c)</sub> Juncti	Sunction to case	Total		° C/W
R <sub>th(c)</sub>	Coupling thermal resistance		0.1	

When the diodes are used simultaneously:

 $\Delta T_{j(diode1)} = P_{(diode1)} \times R_{th(j-c)} (per diode) + P_{(diode2)} \times R_{th(c)}$ 

#### Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	Reverse leakage current	$T_j = 25^\circ C$	V V			15	
'R` ′	neverse leakage current	$T_j = 125^\circ C$ $V_R = V_{RRM}$			15	150	μA
		$T_j = 25^\circ C$				1.45	
V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 100° C	I <sub>F</sub> = 30 A		1.05	1.3	V	
		T <sub>j</sub> = 150° C			0.95	1.20	

1. Pulse test:  $t_p = 5 \text{ ms}, \delta < 2 \%$ 

2. Pulse test:  $t_p$  = 380 µs,  $\delta$  < 2 %

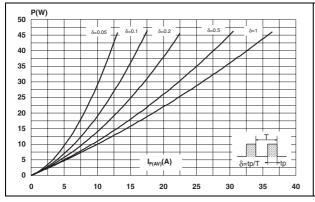
To evaluate the conduction losses use the following equation: P = 0.9 x  $I_{F(AV)}$  + 0.01 x  ${I_F}^2_{(RMS)}$ 

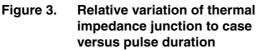


Table 4.	Dynamic	characteristics
----------	---------	-----------------

Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$I_F = 1 \text{ A, } dI_F/dt = -50 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$			65	
t <sub>rr</sub>	Reverse recovery time	$I_F = 1 \text{ A, } dI_F/dt = -100 \text{ A/}\mu\text{s},$ $V_R = 30 \text{ V, } T_j = 25^{\circ} \text{ C}$		31	45	ns
	$    I_F = 1 \text{ A, } dI_F/dt = -200 \text{ A}/\mu\text{s}, \\ V_R = 30 \text{ V, } T_j = 25^\circ \text{ C} $		24	35		
I <sub>RM</sub>	Reverse recovery current	I <sub>F</sub> = 30 A, dI <sub>F</sub> /dt = -200 A/μs, V <sub>R</sub> = 320 V, T <sub>j</sub> = 125° C		10	14	А
S	Softness factor	I <sub>F</sub> = 30 A, dI <sub>F</sub> /dt = -200 A/μs, V <sub>R</sub> = 320 V, T <sub>j</sub> = 125° C		0.4		
t <sub>fr</sub>	Forward recovery time	$    I_F = 30 \ A \qquad dI_F/dt = 100 \ A/\mu s \\ V_{FR} = 1.5 \ x \ V_{Fmax}, \ T_j = 25^\circ \ C $		250		ns
V <sub>FP</sub>	Forward recovery voltage	$I_F$ = 30 A, dI <sub>F</sub> /dt = 100 A/µs, T <sub>j</sub> = 25° C		2.9		V

## Figure 1. Conduction losses versus average current





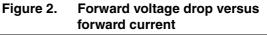
1

шù

tp(s)

1.E-01

1.E+00



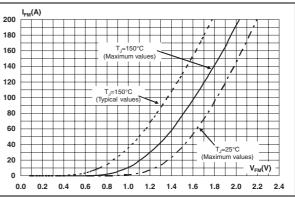
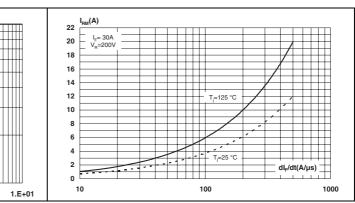


Figure 4. Pe

Peak reverse recovery current versus dl<sub>F</sub>/dt (typical values)



 Zth(j-c)/Rth(j-c)

 1.0
 Single pulse

1.E-02

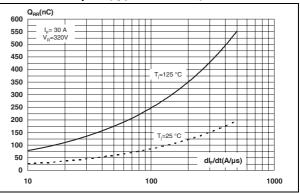


0.1

1.E-03

#### Figure 5. **Reverse recovery time versus** dl<sub>F</sub>/dt (typical values) t<sub>RR</sub>(ns) 160 150 I<sub>F</sub>= 60A V<sub>R</sub>=200V 140 130 120 110 100 ₽ T<sub>j</sub>=125 °C 90 80 70 60 50 40 30 Tj=25 °C 20 10 dl<sub>F</sub>/dt(A/µs) 0 10 100 1000

#### Figure 6. Reverse recovery charges versus dl<sub>F</sub>/dt (typical values)



#### Figure 7. Relative variations of dynamic parameters versus junction temperature

Figure 8. Transient peak forward voltage versus dl<sub>F</sub>/dt (typical values)

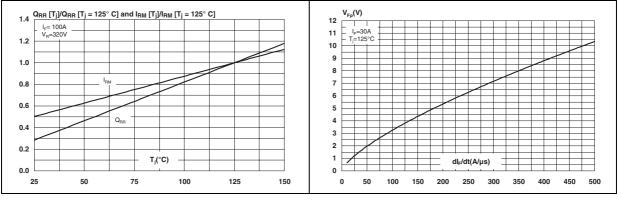
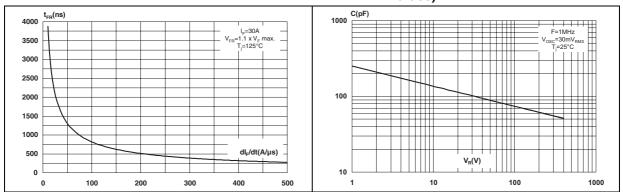


Figure 9. Forward recovery time versus dl<sub>F</sub>/dt Figure 10. (typical values)

Junction capacitance versus reverse voltage applied (typical values)



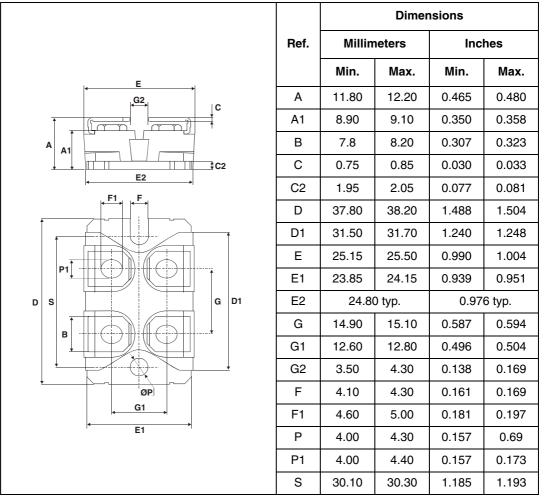


### 2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 5. ISOTOP dimensions



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

57

## **3** Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode
STTH61R04TV1	STTH61R04TV1	ISOTOP	27 g	10	Tube
STTH61R04TV2	STTH61R04TV2	ISOTOP	27 g	10	Tube

## 4 Revision history

Date	Revision	Description of Changes
31-Mar-2007	1	First issue



#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2007 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

